

N-Channel Enhancement Mode Power MOSFET

Description

The G40N03A uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

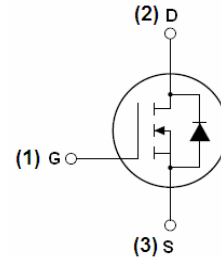
General Features

- $V_{DS} = 30V, I_D = 40A$
 $R_{DS(ON)} < 6.5m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 10m\Omega @ V_{GS} = 4.5V$
- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- SMPS and general purpose applications
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

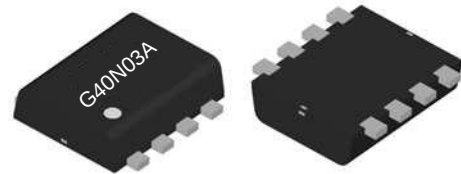


Schematic diagram

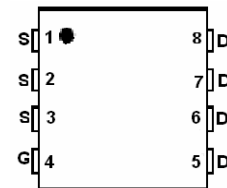
DFN 3x3

Top View

Bottom View



Marking and pin Assignment



DFN 3x3 EP top view

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	40	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	28	A
Pulsed Drain Current	I_{DM}	120	A
Maximum Power Dissipation	P_D	35	W
Derating factor		0.28	W/ $^\circ C$
Single pulse avalanche energy ^(Note 5)	E_{AS}	140	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	3.6	$^{\circ}\text{C/W}$
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Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

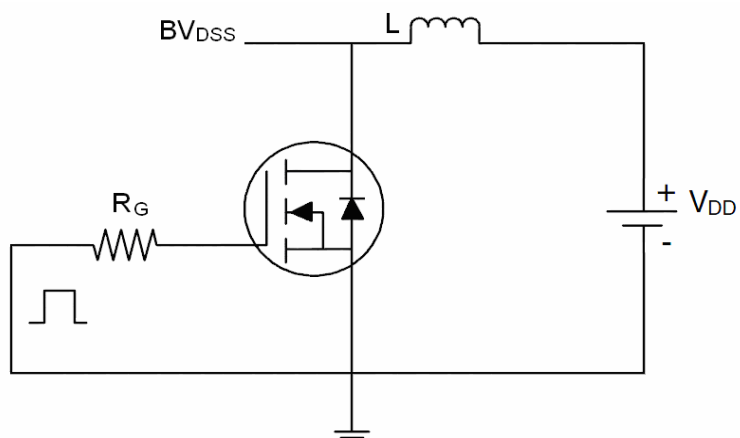
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	1	1.5	2.3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =10A	-	5.1	6.5	mΩ
		V _{GS} =4.5V, I _D =10A	-	8.2	10	
Forward Transconductance	g _{FS}	V _{DS} =5V,I _D =20A	15	-	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{ISS}	V _{DS} =15V,V _{GS} =0V, F=1.0MHz	-	1560	-	PF
Output Capacitance	C _{OSS}		-	280	-	PF
Reverse Transfer Capacitance	C _{RSS}		-	155	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V,I _D =10A V _{GS} =10V,R _{GEN} =1.8Ω	-	11	-	nS
Turn-on Rise Time	t _r		-	9	-	nS
Turn-Off Delay Time	t _{d(off)}		-	33	-	nS
Turn-Off Fall Time	t _f		-	7	-	nS
Total Gate Charge	Q _g	V _{DS} =15V,I _D =9A, V _{GS} =10V	-	19	-	nC
Gate-Source Charge	Q _{gs}		-	2.8	-	nC
Gate-Drain Charge	Q _{gd}		-	2.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V,I _S =20A	-	0.83	1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	25	A
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 10A di/dt = 100A/μs(Note3)	-	25	37	nS
Reverse Recovery Charge	Q _{rr}		-	14	22	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

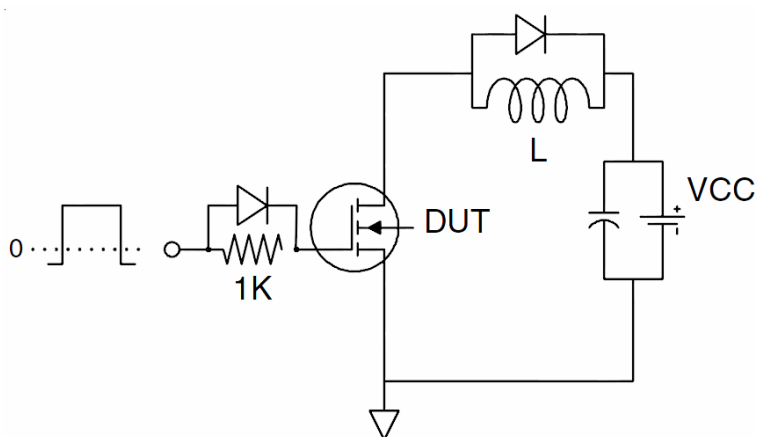
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=15V, V_G=10V, L=0.1\text{mH}, R_g=25\Omega$

Test Circuit

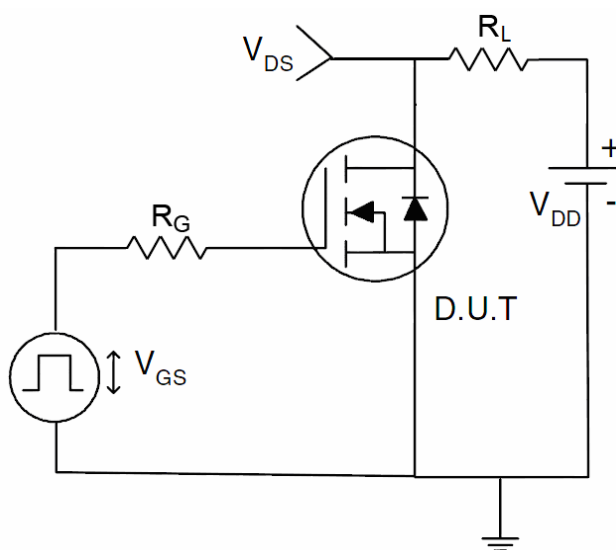
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

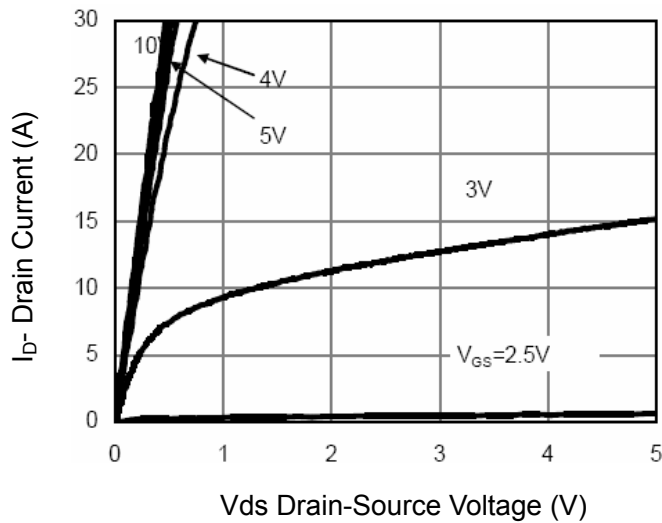


Figure 1 Output Characteristics

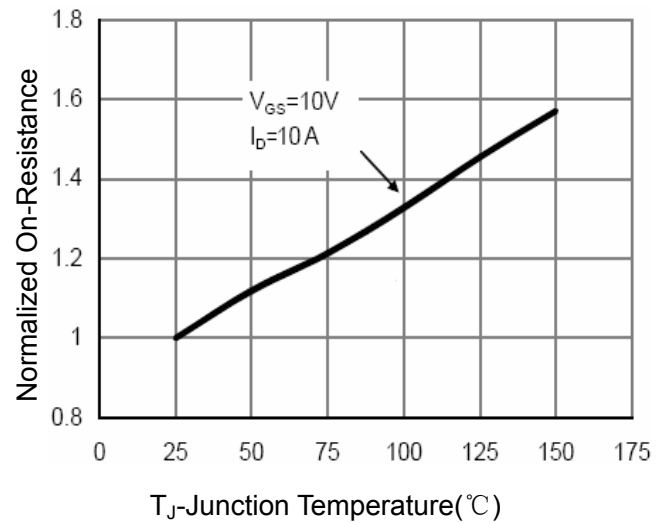


Figure 4 R_{dson} -Junction Temperature

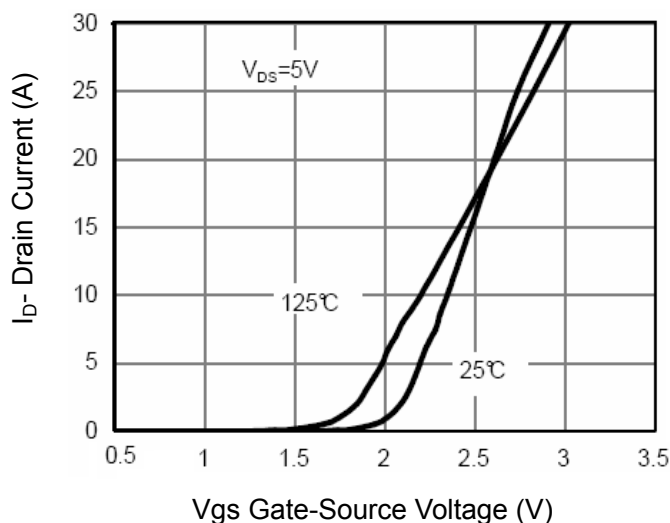


Figure 2 Transfer Characteristics

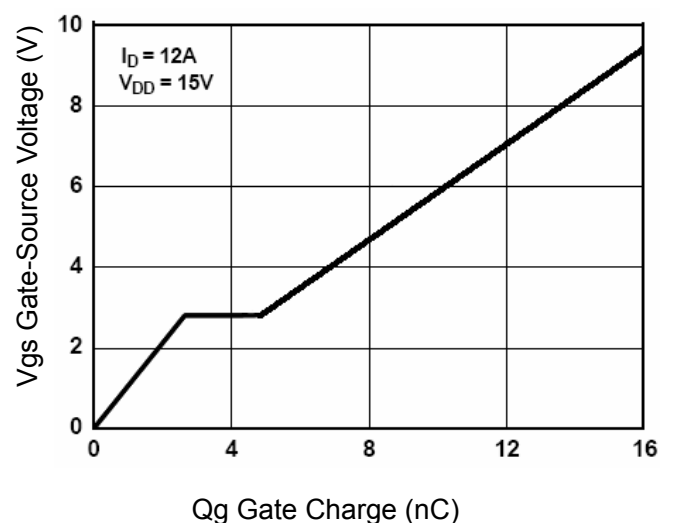


Figure 5 Gate Charge

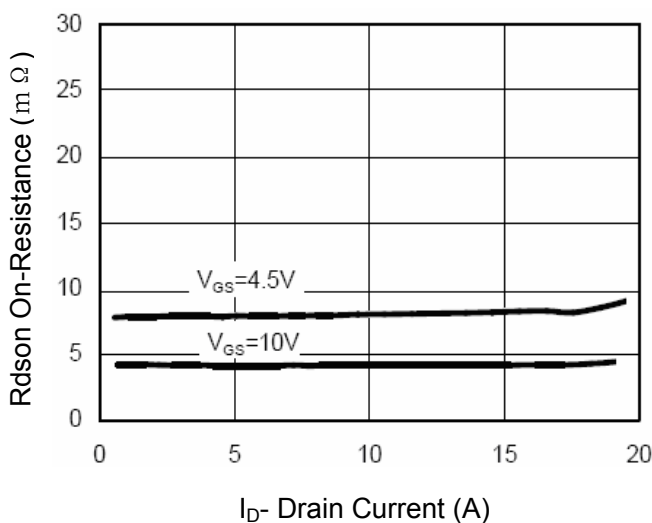


Figure 3 R_{dson} - Drain Current

Figure 1 Output Characteristics

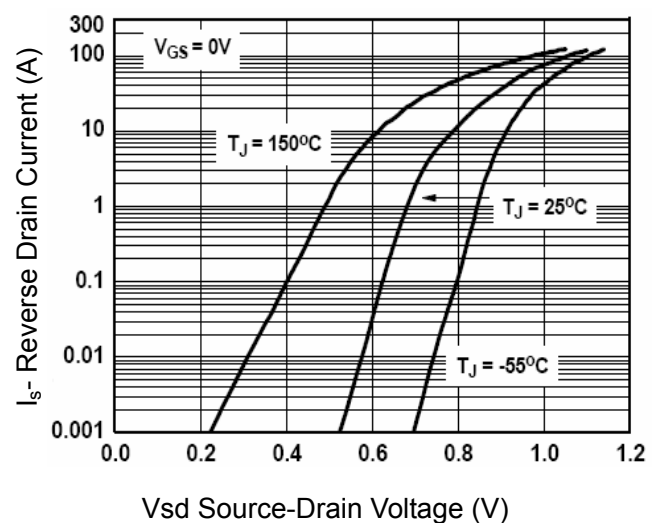
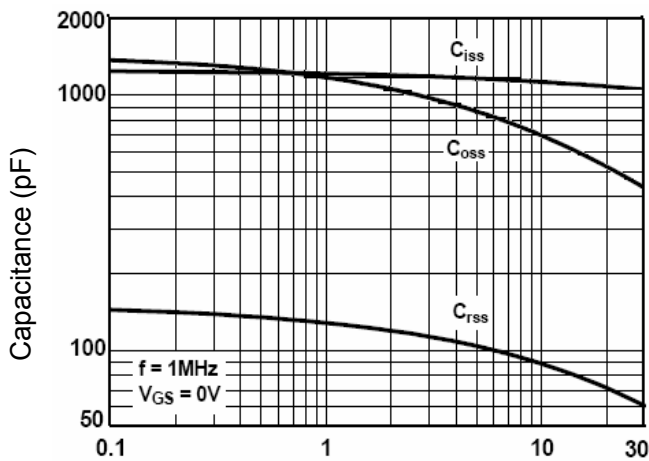
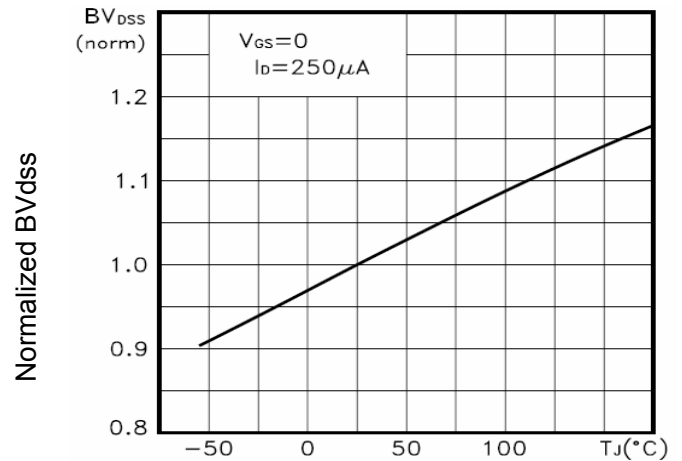


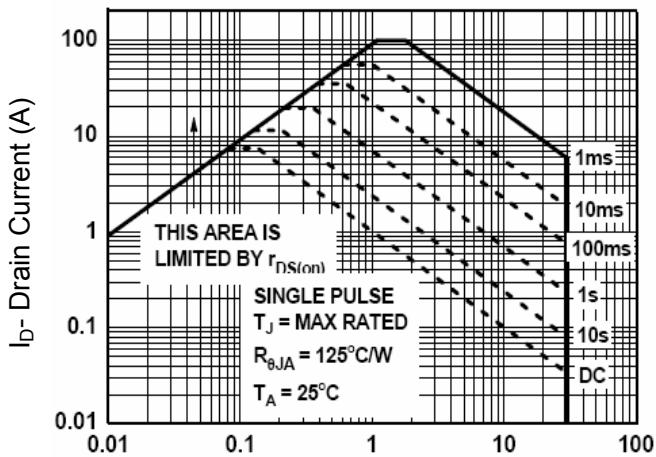
Figure 6 Source- Drain Diode Forward



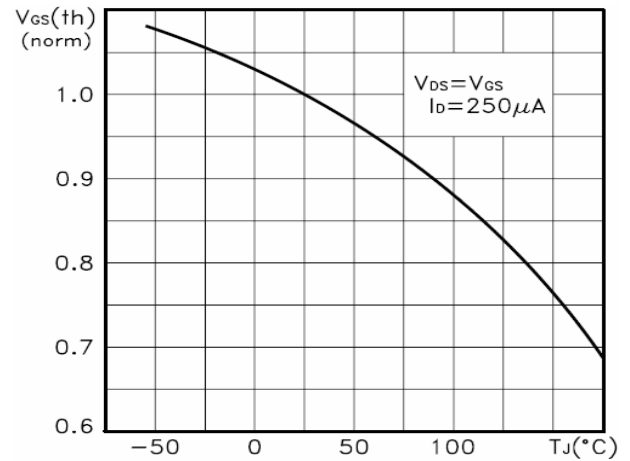
Vds Drain-Source Voltage (V)
Figure 7 Capacitance vs Vds



TJ-Junction Temperature(°C)
Figure 9 BV_{DSS} vs Junction Temperature



Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area



TJ-Junction Temperature(°C)
Figure 10 V_{GS(th)} vs Junction Temperature

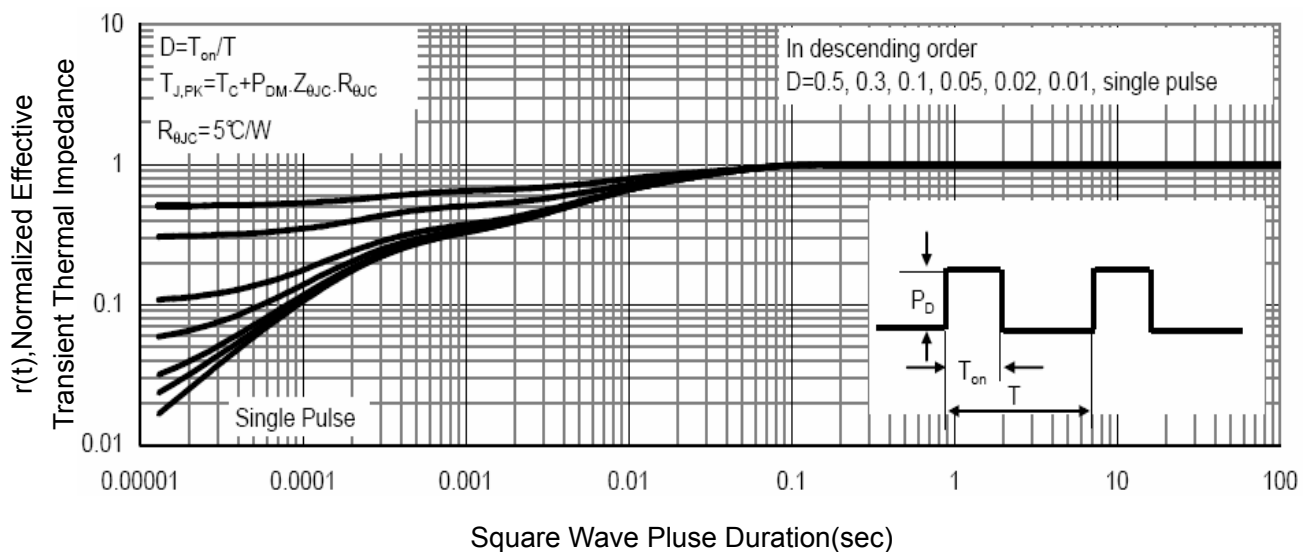
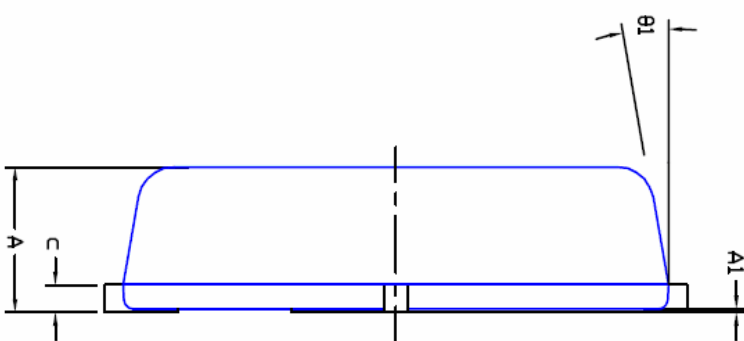
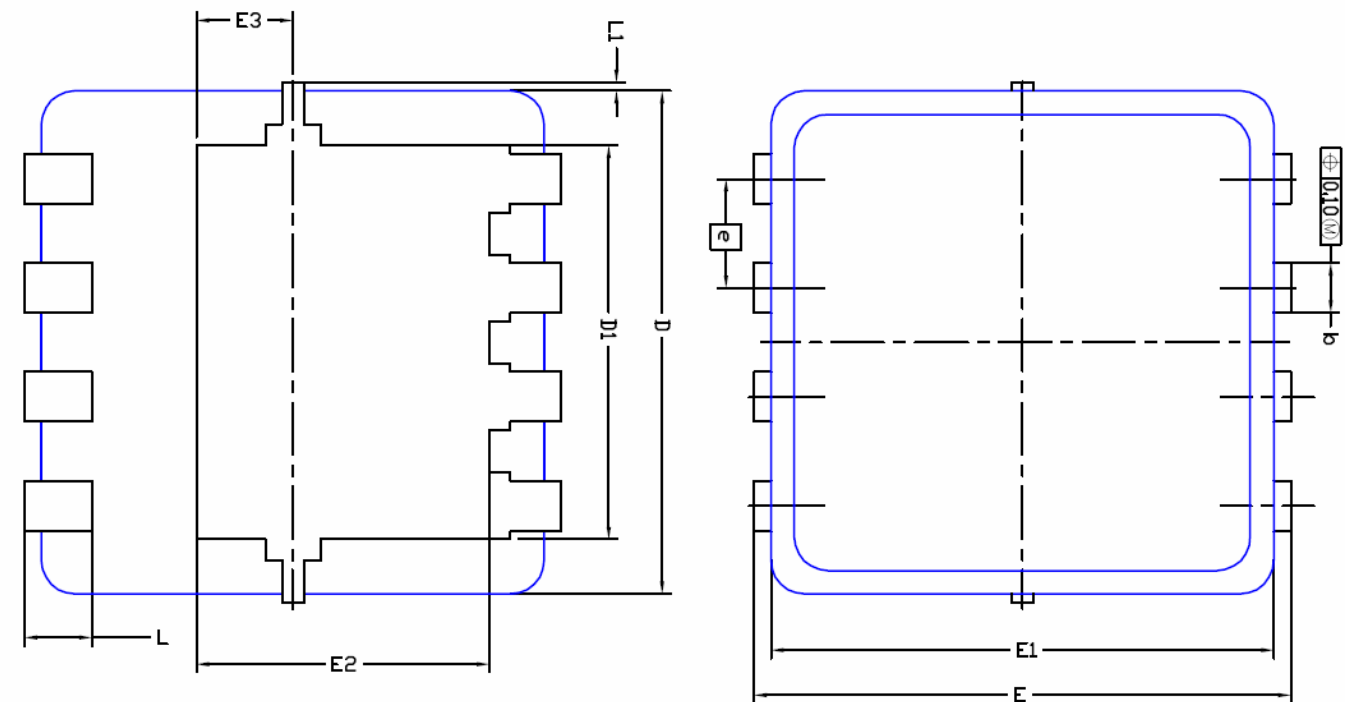


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN3X3 EP Package Information



DIM.	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.80	0.900	0.0276	0.0315	0.0354
A1	0.00	---	0.05	0.000	---	0.002
b	0.24	0.30	0.35	0.009	0.012	0.014
c	0.10	0.152	0.25	0.004	0.006	0.010
D	3.00 BSC			0.118 BSC		
D1	2.35 BSC			0.093 BSC		
E	3.20 BSC			0.126 BSC		
E1	3.00 BSC			0.118 BSC		
E2	1.75 BSC			0.069 BSC		
E3	0.575 BSC			0.023 BSC		
e	0.65 BSC			0.026 BSC		
L	0.30	0.40	0.50	0.0118	0.0157	0.0197
L1	0	---	0.100	0	---	0.004
θ1	0°	10°	12°	0°	10°	12°